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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	154
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p600l-pq208

IGLOO nano and IGLOO PLUS I/O State in Flash*Freeze Mode

In IGLOO nano and IGLOO PLUS devices, users have multiple options in how to configure I/Os during Flash*Freeze mode:

1. Hold the previous state
2. Set I/O pad to weak pull-up or pull-down
3. Tristate I/O pads

The I/O configuration must be configured by the user in the I/O Attribute Editor or in a PDC constraint file, and can be done on a pin-by-pin basis. The output hold feature will hold the output in the last registered state, using the I/O pad weak pull-up or pull-down resistor when the FF pin is asserted. When inputs are configured with the hold feature enabled, the FPGA core side of the input will hold the last valid state of the input pad before the device entered Flash*Freeze mode. The input pad can be driven to any value, configured as tristate, or configured with the weak pull-up or pull-down I/O pad feature during Flash*Freeze mode without affecting the hold state. If the weak pull-up or pull-down feature is used without the output hold feature, the input and output pads will maintain the configured weak pull-up or pull-down status during Flash*Freeze mode and normal operation. If a fixed weak pull-up or pull-down is defined on an output buffer or as bidirectional in output mode, and a hold state is also defined for the same pin, the pin will be configured in hold state mode during Flash*Freeze mode. During normal operation, the pin will be configured with the predefined weak pull-up or pull-down. Any I/Os that do not use the hold state or I/O pad weak pull-up or pull-down features will be tristated during Flash*Freeze mode and the FPGA core will be driven High by inputs. Inputs that are tristated during Flash*Freeze mode may be left floating without any reliability concern or impact to power consumption.

Table 2-6 shows the I/O pad state based on the configuration and buffer type.

Note that configuring weak pull-up or pull-down for the FF pin is not allowed.

Table 2-6 • **IGLOO nano and IGLOO PLUS Flash*Freeze Mode (type 1 and type 2)—I/O Pad State**

Buffer Type		Hold State	I/O Pad Weak Pull-Up/-Down	I/O Pad State in Flash*Freeze Mode
Input		Enabled	Enabled	Weak pull-up/pull-down [1]
		Disabled	Enabled	Weak pull-up/pull-down [2]
		Enabled	Disabled	Tristate [1]
		Disabled	Disabled	Tristate [2]
Output		Enabled	"Don't care"	Weak pull to hold state
		Disabled	Enabled	Weak pull-up/pull-down
		Disabled	Disabled	Tristate
Bidirectional / Tristate Buffer	E = 0 (input/tristate)	Enabled	Enabled	Weak pull-up/pull-down [1]
		Disabled	Enabled	Weak pull-up/pull-down [2]
		Enabled	Disabled	Tristate [1]
		Disabled	Disabled	Tristate [2]
	E = 1 (output)	Enabled	"Don't care"	Weak pull to hold state [3]
		Disabled	Enabled	Weak pull-up/pull-down
		Disabled	Disabled	Tristate

Notes:

1. *Internal core logic driven by this input buffer will be set to the value this I/O had when entering Flash*Freeze mode.*
2. *Internal core logic driven by this input buffer will be tied High as long as the device is in Flash*Freeze mode.*
3. *For bidirectional buffers: Internal core logic driven by the input portion of the bidirectional buffer will be set to the hold state.*

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A
	The "Global Architecture" section and "VersaNet Global Network Distribution" section were revised for clarity (SARs 20646, 24779).	47, 49
	The "I/O Banks and Global I/Os" section was moved earlier in the document, renamed to "Chip and Quadrant Global I/Os", and revised for clarity. Figure 3-4 • Global Connections Details, Figure 3-6 • Global Inputs, Table 3-2 • Chip Global Pin Name, and Table 3-3 • Quadrant Global Pin Name are new (SARs 20646, 24779).	51
	The "Clock Aggregation Architecture" section was revised (SARs 20646, 24779).	57
	Figure 3-7 • Chip Global Aggregation was revised (SARs 20646, 24779).	59
	The "Global Macro and Placement Selections" section is new (SARs 20646, 24779).	64
v1.4 (December 2008)	The "Global Architecture" section was updated to include 10 k devices, and to include information about VersaNet global support for IGLOO nano devices.	47
	The Table 3-1 • Flash-Based FPGAs was updated to include IGLOO nano and ProASIC3 nano devices.	48
	The "VersaNet Global Network Distribution" section was updated to include 10 k devices and to note an exception in global lines for nano devices.	49
	Figure 3-2 • Simplified VersaNet Global Network (30 k gates and below) is new.	50
	The "Spine Architecture" section was updated to clarify support for 10 k and nano devices.	57
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to include IGLOO nano and ProASIC3 nano devices.	57
	The figure in the CLKBUF_LVDS/LVPECL row of Table 3-8 • Clock Macros was updated to change CLKBIBUF to CLKBUF.	62
v1.3 (October 2008)	A third bullet was added to the beginning of the "Global Architecture" section: In Fusion devices, the west CCC also contains a PLL core. In the two larger devices (AFS600 and AFS1500), the west and east CCCs each contain a PLL.	47
	The "Global Resource Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	48
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to include A3PE600/L in the device column.	57
	Table note 1 was revised in Table 3-9 • I/O Standards within CLKBUF to include AFS600 and AFS1500.	63
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 3-1 • Flash-Based FPGAs: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	48

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4 – Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Introduction

This document outlines the following device information: Clock Conditioning Circuit (CCC) features, PLL core specifications, functional descriptions, software configuration information, detailed usage information, recommended board-level considerations, and other considerations concerning clock conditioning circuits and global networks in low power flash devices or mixed signal FPGAs.

Overview of Clock Conditioning Circuitry

In Fusion, IGLOO, and ProASIC3 devices, the CCCs are used to implement frequency division, frequency multiplication, phase shifting, and delay operations. The CCCs are available in six chip locations—each of the four chip corners and the middle of the east and west chip sides. For device-specific variations, refer to the "Device-Specific Layout" section on page 94.

The CCC is composed of the following:

- PLL core
- 3 phase selectors
- 6 programmable delays and 1 fixed delay that advances/delays phase
- 5 programmable frequency dividers that provide frequency multiplication/division (not shown in Figure 4-6 on page 87 because they are automatically configured based on the user's required frequencies)
- 1 dynamic shift register that provides CCC dynamic reconfiguration capability

Figure 4-1 provides a simplified block diagram of the physical implementation of the building blocks in each of the CCCs.

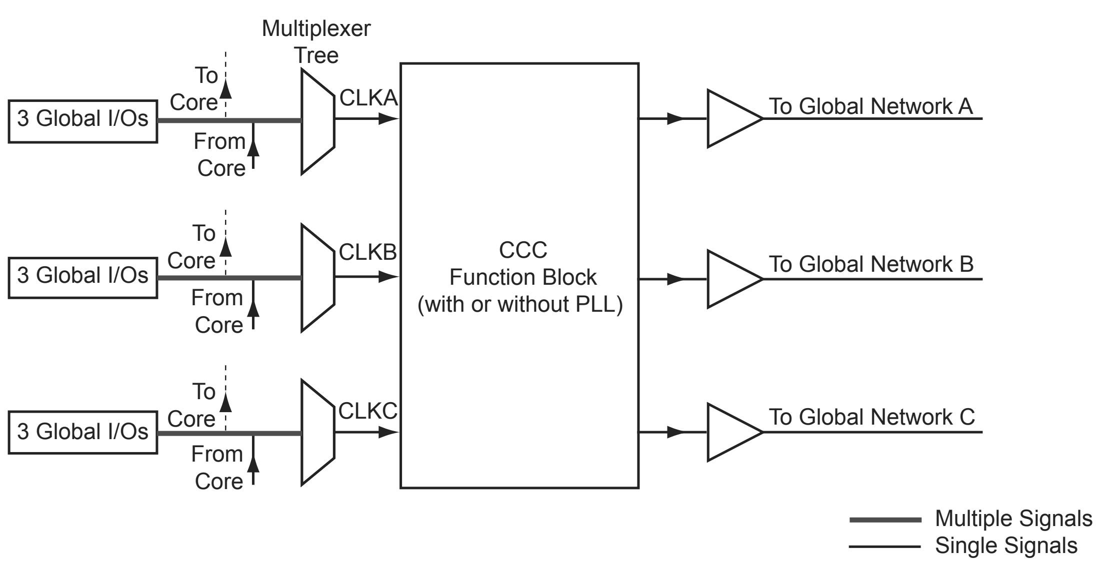


Figure 4-1 • **Overview of the CCCs Offered in Fusion, IGLOO, and ProASIC3**

YB and YC are identical to GLB and GLC, respectively, with the exception of a higher selectable final output delay. The SmartGen PLL Wizard will configure these outputs according to user specifications and can enable these signals with or without the enabling of Global Output Clocks.

The above signals can be enabled in the following output groupings in both internal and external feedback configurations of the static PLL:

- One output – GLA only
- Two outputs – GLA + (GLB and/or YB)
- Three outputs – GLA + (GLB and/or YB) + (GLC and/or YC)

PLL Macro Block Diagram

As illustrated, the PLL supports three distinct output frequencies from a given input clock. Two of these (GLB and GLC) can be routed to the B and C global network access, respectively, and/or routed to the device core (YB and YC).

There are five delay elements to support phase control on all five outputs (GLA, GLB, GLC, YB, and YC).

There are delay elements in the feedback loop that can be used to advance the clock relative to the reference clock.

The PLL macro reference clock can be driven in the following ways:

1. By an INBUF* macro to create a composite macro, where the I/O macro drives the global buffer (with programmable delay) using a hardwired connection. In this case, the I/O must be placed in one of the dedicated global I/O locations.
2. Directly from the FPGA core.
3. From an I/O that is routed through the FPGA regular routing fabric. In this case, users must instantiate a special macro, PLLINT, to differentiate from the hardwired I/O connection described earlier.

During power-up, the PLL outputs will toggle around the maximum frequency of the voltage-controlled oscillator (VCO) gear selected. Toggle frequencies can range from 40 MHz to 250 MHz. This will continue as long as the clock input (CLKA) is constant (HIGH or LOW). This can be prevented by LOW assertion of the POWERDOWN signal.

The visual PLL configuration in SmartGen, a component of the Libero SoC and Designer tools, will derive the necessary internal divider ratios based on the input frequency and desired output frequencies selected by the user.

```
DLYGLC[4:0]     00000
DLYYB[4:0]      00000
DLYYC[4:0]      00000
VCOSEL[2:0]     100

Primary Clock Frequency 33.000
Primary Clock Phase Shift 0.000
Primary Clock Output Delay from CLKA 1.695

Secondary1 Clock Frequency 40.000
Secondary1 Clock Phase Shift 0.000
Secondary1 Clock Global Output Delay from CLKB 0.200

Secondary2 Clock Frequency 50.000
Secondary2 Clock Phase Shift 0.000
Secondary2 Clock Global Output Delay from CLKC 0.200

######################################
# Dynamic Stream Data
######################################
--------------------------------------
|NAME    |SDIN     |VALUE   |TYPE     |
--------------------------------------
|FINDIV  |[6:0]    |0000101 |EDIT     |
|FBDIV   |[13:7]   |0100000 |EDIT     |
|OADIV   |[18:14]  |00100   |EDIT     |
|OBDIV   |[23:19]  |00000   |EDIT     |
|OCDIV   |[28:24]  |00000   |EDIT     |
|OAMUX   |[31:29]  |100     |EDIT     |
|OBMUX   |[34:32]  |000     |EDIT     |
|OCMUX   |[37:35]  |000     |EDIT     |
|FBSEL   |[39:38]  |01      |EDIT     |
|FBDLY   |[44:40]  |00000   |EDIT     |
|XDLYSEL |[45]     |0       |EDIT     |
|DLYGLA  |[50:46]  |00000   |EDIT     |
|DLYGLB  |[55:51]  |00000   |EDIT     |
|DLYGLC  |[60:56]  |00000   |EDIT     |
|DLYYB   |[65:61]  |00000   |EDIT     |
|DLYYC   |[70:66]  |00000   |EDIT     |
|STATASEL|[71]     |X       |MASKED   |
|STATBSEL|[72]     |X       |MASKED   |
|STATCSEL|[73]     |X       |MASKED   |
|VCOSEL  |[76:74]  |100     |EDIT     |
|DYNASEL |[77]     |X       |MASKED   |
|DYNBSEL |[78]     |X       |MASKED   |
|DYNCSEL |[79]     |X       |MASKED   |
|RESETEN |[80]     |1       |READONLY |
```

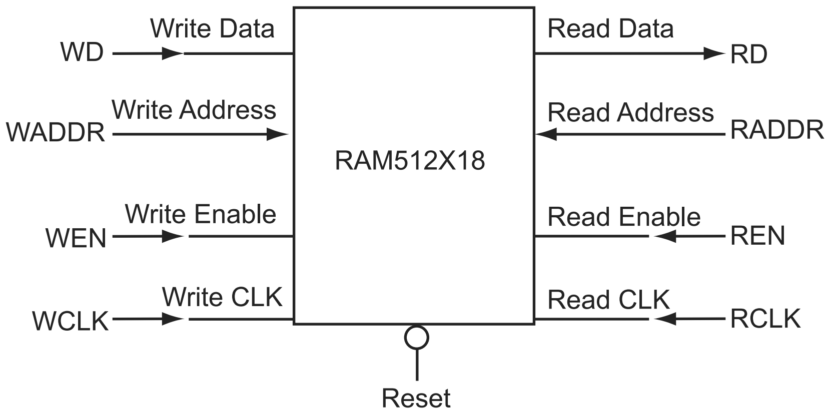
Below is the resultant Verilog HDL description of a legal dynamic PLL core configuration generated by SmartGen:

```
module dyn_pll_macro(POWERDOWN, CLKA, LOCK, GLA, GLB, GLC, SDIN, SCLK, SSHIFT, SUPDATE,
  MODE, SDOUT, CLKB, CLKC);

input POWERDOWN, CLKA;
output  LOCK, GLA, GLB, GLC;
input  SDIN, SCLK, SSHIFT, SUPDATE, MODE;
output  SDOUT;
input  CLKB, CLKC;

  wire VCC, GND;

  VCC VCC_1_net(.Y(VCC));
  GND GND_1_net(.Y(GND));
```



Note: For timing diagrams of the RAM signals, refer to the appropriate family datasheet.

Figure 6-5 **• 512X18 Two-Port RAM Block Diagram**

Signal Descriptions for RAM512X18

RAM512X18 has slightly different behavior from RAM4K9, as it has dedicated read and write ports.

WW and RW

These signals enable the RAM to be configured in one of the two allowable aspect ratios (Table 6-5).

Table 6-5 **• Aspect Ratio Settings for WW[1:0]**

WW[1:0]	RW[1:0]	D×W
01	01	512×9
10	10	256×18
00, 11	00, 11	Reserved

WD and RD

These are the input and output data signals, and they are 18 bits wide. When a 512×9 aspect ratio is used for write, WD[17:9] are unused and must be grounded. If this aspect ratio is used for read, RD[17:9] are undefined.

WADDR and RADDR

These are read and write addresses, and they are nine bits wide. When the 256×18 aspect ratio is used for write or read, WADDR[8] and RADDR[8] are unused and must be grounded.

WCLK and RCLK

These signals are the write and read clocks, respectively. They can be clocked on the rising or falling edge of WCLK and RCLK.

WEN and REN

These signals are the write and read enables, respectively. They are both active-low by default. These signals can be configured as active-high.

RESET

This active-low signal resets the control logic, forces the output hold state registers to zero, disables reads and writes from the SRAM block, and clears the data hold registers when asserted. It does not reset the contents of the memory array.

While the RESET signal is active, read and write operations are disabled. As with any asynchronous reset signal, care must be taken not to assert it too close to the edges of active read and write clocks.

PIPE

This signal is used to specify pipelined read on the output. A LOW on PIPE indicates a nonpipelined read, and the data appears on the output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the output in the next clock cycle.

Software Support

The SmartGen core generator is the easiest way to select and configure the memory blocks (Figure 6-12). SmartGen automatically selects the proper memory block type and aspect ratio, and cascades the memory blocks based on the user's selection. SmartGen also configures any additional signals that may require tie-off.

SmartGen will attempt to use the minimum number of blocks required to implement the desired memory. When cascading, SmartGen will configure the memory for width before configuring for depth. For example, if the user requests a 256×8 FIFO, SmartGen will use a 512×9 FIFO configuration, not 256×18.

Figure 6-12 **• SmartGen Core Generator Interface**

I/O Features

Low power flash devices support multiple I/O features that make board design easier. For example, an I/O feature like Schmitt Trigger in the ProASIC3E input buffer saves the board space that would be used by an external Schmitt trigger for a slow or noisy input signal. These features are also programmable for each I/O, which in turn gives flexibility in interfacing with other components. The following is a detailed description of all available features in low power flash devices.

I/O Programmable Features

Low power flash devices offer many flexible I/O features to support a wide variety of board designs. Some of the features are programmable, with a range for selection. Table 7-7 lists programmable I/O features and their ranges.

Table 7-7 **• Programmable I/O Features (user control via I/O Attribute Editor)**

Feature[1]	Description	Range
Slew Control	Output slew rate	HIGH, LOW
Output Drive (mA)	Output drive strength	2, 4, 6, 8, 12, 16, 24
Skew Control	Output tristate enable delay option	ON, OFF
Resistor Pull	Resistor pull circuit	Up, Down, None
Input Delay[2]	Input delay	OFF, 0–7
Schmitt Trigger	Schmitt trigger for input only	ON, OFF

Notes:

1. *Limitations of these features with respect to different devices are discussed in later sections.*
2. *Programmable input delay is applicable only to ProASIC3EL and RT ProASIC3 devices.*

Hot-Swap Support

A pull-up clamp diode must not be present in the I/O circuitry if the hot-swap feature is used. The 3.3 V PCI standard requires a pull-up clamp diode on the I/O, so it cannot be selected if hot-swap capability is required. The A3P030 device does not support 3.3 V PCI, so it is the only device in the ProASIC3 family that supports the hot-swap feature. All devices in the ProASIC3E family are hot-swappable. All standards except LVCMOS 2.5/5.0 V and 3.3 V PCI/PCI-X support the hot-swap feature.

The hot-swap feature appears as a read-only check box in the I/O Attribute Editor that shows whether an I/O is hot-swappable or not. Refer to the *"Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373* for details on hot-swapping.

Hot-swapping (also called hot-plugging) is the operation of hot insertion or hot removal of a card in a powered-up system. The levels of hot-swap support and examples of related applications are described in Table 7-8 on page 189 to Table 7-11 on page 190. The I/Os also need to be configured in hot-insertion mode if hot-plugging compliance is required. The AGL030 and A3P030 devices have an I/O structure that allows the support of Level 3 and Level 4 hot-swap with only two levels of staging.

Date	Change	Page
June 2011 (continued)	The following sentence was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 22634): "All these versions use a 3.3 V–tolerant CMOS input buffer and a push-pull output buffer."	184
	Hot-insertion was changed to "No" for other IGLOO and all ProASIC3 devices in Table 7-12 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in IGLOO and ProASIC3 Devices (SAR 24526).	193
	The "Electrostatic Discharge Protection" section was revised to remove references to tolerances (refer to the *Reliability Report* for tolerances). The Machine Model (MM) is not supported and was deleted from this section (SAR 24385).	192
	The "I/O Interfacing" section was revised to state that low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected, removing "without adding any extra circuitry," which was incorrect (SAR 21404).	208
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.4 (December 2008)	The terminology in the "Low Power Flash Device I/O Support" section was revised.	176
v1.3 (October 2008)	The "Low Power Flash Device I/O Support" section was revised to include new families and make the information more concise.	176
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 7-1 • Flash-Based FPGAs: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	176
v1.1 (March 2008)	Originally, this document contained information on all IGLOO and ProASIC3 families. With the addition of new families and to highlight the differences between the features, the document has been separated into 3 documents: This document contains information specific to IGLOO, ProASIC3, and ProASIC3L. "I/O Structures in IGLOOe and ProASIC3E Devices" in the *ProASIC3E FPGA Fabric User's Guide* contains information specific to IGLOOe, ProASIC3E, and ProASIC3EL I/O features. "I/O Structures in IGLOO PLUS Devices" in the *IGLOO PLUS FPGA Fabric User's Guide* contains information specific to IGLOO PLUS I/O features.	N/A

8 – I/O Structures in IGLOOe and ProASIC3E Devices

Introduction

Low power flash devices feature a flexible I/O structure, supporting a range of mixed voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V) through bank-selectable voltages. IGLOO®e, ProASIC®3EL, and ProASIC3E families support Pro I/Os.

Users designing I/O solutions are faced with a number of implementation decisions and configuration choices that can directly impact the efficiency and effectiveness of their final design. The flexible I/O structure, supporting a wide variety of voltages and I/O standards, enables users to meet the growing challenges of their many diverse applications. The Libero SoC software provides an easy way to implement I/O that will result in robust I/O design.

This document first describes the two different I/O types in terms of the standards and features they support. It then explains the individual features and how to implement them in Libero SoC.

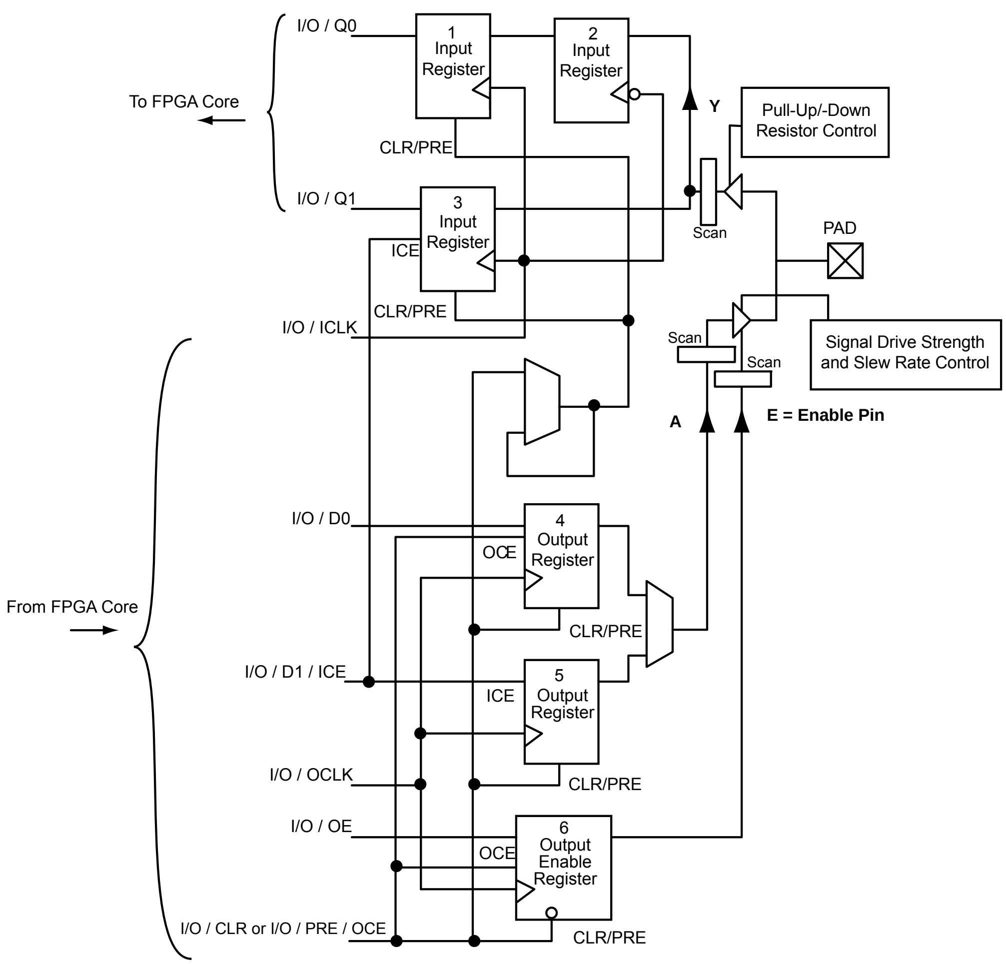


Figure 8-1 • **DDR Configured I/O Block Logical Representation**

This current draw can occur in the following cases:

- In Active and Static modes:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High
  - Output buffers with pull-up, driven Low
  - Output buffers with pull-down, driven High
  - Tristate buffers with pull-up, driven Low
  - Tristate buffers with pull-down, driven High
- In Flash*Freeze mode:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High

Electrostatic Discharge Protection

Low power flash devices are tested per JEDEC Standard JESD22-A114-B.

These devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

All IGLOO and ProASIC3 devices are tested to the Human Body Model (HBM) and the Charged Device Model (CDM).

Each I/O has two clamp diodes. One diode has its positive (P) side connected to the pad and its negative (N) side connected to VCCI. The second diode has its P side connected to GND and its N side connected to the pad. During operation, these diodes are normally biased in the off state, except when transient voltage is significantly above VCCI or below GND levels.

In 30 k gate devices, the first diode is always off. In other devices, the clamp diode is always on and cannot be switched off.

By selecting the appropriate I/O configuration, the diode is turned on or off. Refer to Table 8-13 for more information about the I/O standards and the clamp diode.

The second diode is always connected to the pad, regardless of the I/O configuration selected.

***Table 8-13* • I/O Hot-Swap and 5 V Input Tolerance Capabilities in IGLOOe and ProASIC3E Devices**

I/O Assignment	Clamp Diode	Hot Insertion	5 V Input Tolerance	Input Buffer	Output Buffer
3.3 V LVTTL/LVCMOS	No	Yes	Yes[1]	Enabled/Disabled	
3.3 V PCI, 3.3 V PCI-X	Yes	No	Yes[1]	Enabled/Disabled	
LVCMOS 2.5 V [2]	No	Yes	No	Enabled/Disabled	
LVCMOS 2.5 V / 5.0 V [2]	Yes	No	Yes[3]	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	No	Enabled/Disabled	
Voltage-Referenced Input Buffer	No	Yes	No	Enabled/Disabled	
Differential, LVDS/B-LVDS/M-LVDS/LVPECL	No	Yes	No	Enabled/Disabled	

Notes:

1. *Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.*
2. *In the* SmartGen Core Reference Guide*, select the LVCMOS5 macro for the LVCMOS 2.5 V / 5.0 V I/O standard or the LVCMOS25 macro for the LVCMOS 2.5 V I/O standard.*
3. *Can be implemented with an external resistor and an internal clamp diode.*

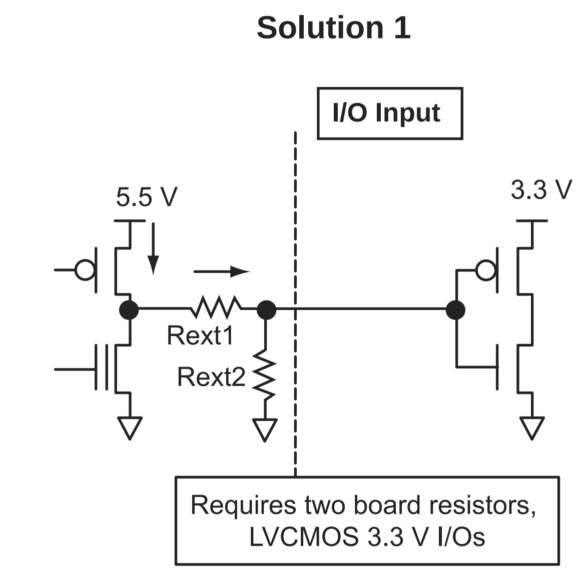


Figure 8-10 **• Solution 1**

Solution 2

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the external resistors and Zener, as shown in Figure 8-11. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.

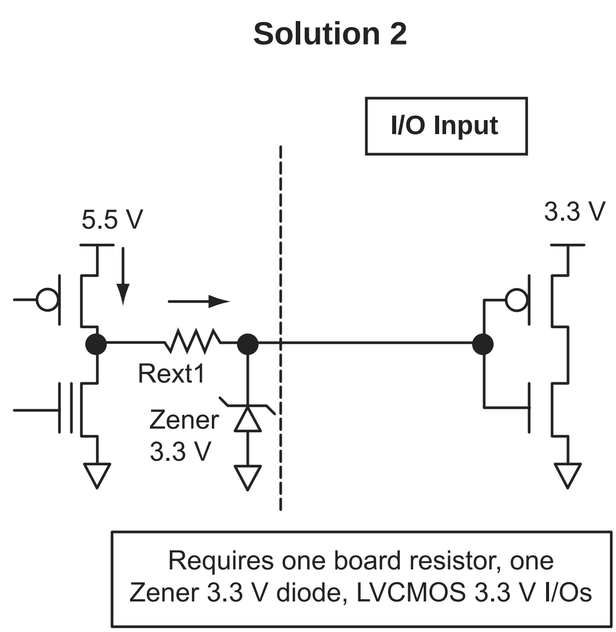


Figure 8-11 **• Solution 2**

User I/O Naming Convention

IGLOOe and ProASIC3E

Due to the comprehensive and flexible nature of IGLOOe and ProASIC3E device user I/Os, a naming scheme is used to show the details of each I/O (Figure 8-20 on page 246). The name identifies to which I/O bank it belongs, as well as the pairing and pin polarity for differential I/Os.

I/O Nomenclature = FF/Gmn/IOuxwByVz

Gmn is only used for I/Os that also have CCC access—i.e., global pins.

FF = Indicates the I/O dedicated for the Flash*Freeze mode activation pin in IGLOOe only

G = Global

m = Global pin location associated with each CCC on the device: A (northwest corner), B (northeast corner), C (east middle), D (southeast corner), E (southwest corner), and F (west middle)

n = Global input MUX and pin number of the associated Global location m, either A0, A1, A2, B0, B1, B2, C0, C1, or C2. Refer to the "Global Resources in Low Power Flash Devices" section on page 47 for information about the three input pins per clock source MUX at CCC location m.

u = I/O pair number in the bank, starting at 00 from the northwest I/O bank and proceeding in a clockwise direction

x = P (Positive) or N (Negative) for differential pairs, or R (Regular—single-ended) for the I/Os that support single-ended and voltage-referenced I/O standards only

w = D (Differential Pair), P (Pair), or S (Single-Ended). D (Differential Pair) if both members of the pair are bonded out to adjacent pins or are separated only by one GND or NC pin; P (Pair) if both members of the pair are bonded out but do not meet the adjacency requirement; or S (Single-Ended) if the I/O pair is not bonded out. For Differential (D) pairs, adjacency for ball grid packages means only vertical or horizontal. Diagonal adjacency does not meet the requirements for a true differential pair.

B = Bank

y = Bank number (0–7). The bank number starts at 0 from the northwest I/O bank and proceeds in a clockwise direction.

V = V_{REF}

z = V_{REF} minibank number (0–4). A given voltage-referenced signal spans 16 pins (typically) in an I/O bank. Voltage banks may have multiple V_{REF} minibanks.

3. Double-click I/O to open the Create Core window, which is shown in Figure 9-3).

***Figure 9-3* • I/O Create Core Window**

As seen in Figure 9-3, there are five tabs to configure the I/O macro: Input Buffers, Output Buffers, Bidirectional Buffers, Tristate Buffers, and DDR.

Input Buffers

There are two variations: Regular and Special.

If the **Regular** variation is selected, only the Width (1 to 128) needs to be entered. The default value for Width is 1.

The **Special** variation has Width, Technology, Voltage Level, and Resistor Pull-Up/-Down options (see Figure 9-3). All the I/O standards and supply voltages (V_{CCI}) supported for the device family are available for selection.

Figure 12-18 • **Security Level Set High to Reprogram Device with AES Key**

Programming with this file is intended for an unsecured environment. The AES key encrypts the programming file with the same AES key already used in the device and utilizes it to program the device.

Reprogramming Devices

Previously programmed devices can be reprogrammed using the steps in the "Generation of the Programming File in a Trusted Environment—Application 1" section on page 313 and "Generation of Security Header Programming File Only—Application 2" section on page 316. In the case where a FlashLock Pass Key has been programmed previously, the user must generate the new programming file with a FlashLock Pass Key that matches the one previously programmed into the device. The software will check the FlashLock Pass Key in the programming file against the FlashLock Pass Key in the device. The keys must match before the device can be unlocked to perform further programming with the new programming file.

Figure 12-10 on page 314 and Figure 12-11 on page 314 show the option **Programming previously secured device(s)**, which the user should select before proceeding. Upon going to the next step, the user will be notified that the same FlashLock Pass Key needs to be entered, as shown in Figure 12-19 on page 322.

Microsemi's Flash Devices Support the JTAG Feature

The flash-based FPGAs listed in Table 16-1 support the JTAG feature and the functions described in this document.

Table 16-1 **• Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC®3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

Note: **The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 16-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 16-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

Internal Pull-Up and Pull-Down

Low power flash device I/Os are equipped with internal weak pull-up/-down resistors that can be used by designers. If used, these internal pull-up/-down resistors will be activated during power-up, once both VCC and VCCI are above their functional activation level. Similarly, during power-down, these internal pull-up/-down resistors will turn off once the first supply voltage falls below its brownout deactivation level.

Cold-Sparing

In cold-sparing applications, voltage can be applied to device I/Os before and during power-up. Cold-sparing applications rely on three important characteristics of the device:

1. I/Os must be tristated before and during power-up.
2. Voltage applied to the I/Os must not power up any part of the device.
3. VCCI should not exceed 3.6 V, per datasheet specifications.

As described in the "Power-Up to Functional Time" section on page 378, Microsemi's low power flash I/Os are tristated before and during power-up until the last voltage supply (VCC or VCCI) is powered up past its functional level. Furthermore, applying voltage to the FPGA I/Os does not pull up VCC or VCCI and, therefore, does not partially power up the device. Table 18-4 includes the cold-sparing test results on A3PE600-PQ208 devices. In this test, leakage current on the device I/O and residual voltage on the power supply rails were measured while voltage was applied to the I/O before power-up.

***Table 18-4* • Cold-Sparing Test Results for A3PE600 Devices**

Device I/O	Residual Voltage (V)		Leakage Current
	VCC	VCCI	
Input	0	0.003	<1 µA
Output	0	0.003	<1 µA

VCCI must not exceed 3.6 V, as stated in the datasheet specification. Therefore, ProASIC3E devices meet all three requirements stated earlier in this section and are suitable for cold-sparing applications.

The following devices and families support cold-sparing:

- IGLOO: AGL015 and AGL030
- All IGLOO nano
- All IGLOO PLUS
- All IGLOOe
- ProASIC3L: A3PE3000L
- ProASIC3: A3P015 and A3P030
- All ProASIC3 nano
- All ProASIC3E
- Military ProASIC3EL: A3PE600L and A3PE3000L
- RT ProASIC3: RT3PE600L and RT3PE3000L

B – Product Support

Microsemi SoC Products Group backs its products with various support services, including Customer Service, Customer Technical Support Center, a website, electronic mail, and worldwide sales offices. This appendix contains information about contacting Microsemi SoC Products Group and using these support services.

Customer Service

Contact Customer Service for non-technical product support, such as product pricing, product upgrades, update information, order status, and authorization.

From North America, call 800.262.1060
From the rest of the world, call 650.318.4460
Fax, from anywhere in the world, 650.318.8044

Customer Technical Support Center

Microsemi SoC Products Group staffs its Customer Technical Support Center with highly skilled engineers who can help answer your hardware, software, and design questions about Microsemi SoC Products. The Customer Technical Support Center spends a great deal of time creating application notes, answers to common design cycle questions, documentation of known issues, and various FAQs. So, before you contact us, please visit our online resources. It is very likely we have already answered your questions.

Technical Support

Visit the Customer Support website (www.microsemi.com/soc/support/search/default.aspx) for more information and support. Many answers available on the searchable web resource include diagrams, illustrations, and links to other resources on the website.

Website

You can browse a variety of technical and non-technical information on the SoC home page, at www.microsemi.com/soc.

Contacting the Customer Technical Support Center

Highly skilled engineers staff the Technical Support Center. The Technical Support Center can be contacted by email or through the Microsemi SoC Products Group website.

Email

You can communicate your technical questions to our email address and receive answers back by email, fax, or phone. Also, if you have design problems, you can email your design files to receive assistance. We constantly monitor the email account throughout the day. When sending your request to us, please be sure to include your full name, company name, and your contact information for efficient processing of your request.

The technical support email address is soc_tech@microsemi.com.